



# **Fast Switching Thyristor**

Replaces March 1998 version, DS4275-2.2

DS4275-3.0 January 2000

**KEY PARAMETERS** 

2500V

9000A

**300V/**μs

**500A/**μs **100**μs

600A

 $\mathbf{V}_{\mathrm{DRM}}$ 

T(RMS)

I<sub>TSM</sub> dV/dt

dl/dt

tq

#### **APPLICATIONS**

- High Power Inverters And Choppers
- UPS
- Railway Traction
- Induction Heating
- AC Motor Drives
- Cycloconverters

# **FEATURES**

- Double Side Cooling
- High Surge Capability
- High Voltage

## **VOLTAGE RATINGS**

Type Number	Repetitive Peak Voltages V <sub>DRM</sub> V <sub>RRM</sub>	Conditions
TF707 25L TF707 24L TF707 22L TF707 20L	2500 2400 2200 2000	$V_{RSM} = V_{RRM} + 100V$ $I_{DRM} = I_{RRM} = 60 \text{mA}$ at $V_{RRM}$ or $V_{DRM}$ & $T_{vj}$

Lower voltage grades available.

Outline type code: MU171.
See Package Details for further information.

## **CURRENT RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>T(AV)</sub>	Mean on-state current	Half sinewave, 50Hz, T <sub>case</sub> = 80°C	380	Α
I <sub>T(RMS)</sub>	RMS value	Half sinewave, 50Hz, T <sub>case</sub> = 80°C	600	А

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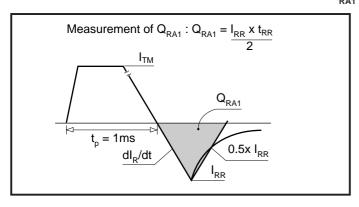
# **SURGE RATINGS**

Symbol	Parameter	Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine; $V_R = 0\% V_{RRM}$ , $T_j = 125$ °C	7.0	kA
l <sup>2</sup> t	I <sup>2</sup> t for fusing	10ms half sine; $V_R = 0\% V_{RRM}$ , $T_j = 125$ °C	245 x 10 <sup>3</sup>	A <sup>2</sup> s

# THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.04	°C/W
		Single side cooled	Anode dc	-	0.072	°C/W
			Cathode dc	-	0.096	°C/W
R <sub>th(c-h)</sub>	Thermal resistance - case to heatsink	Clamping force 15.0kN with mounting compound	Double side	-	0.01	°C/W
			Single side	-	0.02	°C/W
$T_{v_{j}}$	Virtual junction temperature	On-state (conducting)		-	125	°C
		Reverse (blocking)		-	125	°C
T <sub>stg</sub>	Storage temperature range			-40	150	°C
-	Clamping force			14.25	15.75	kN

# MEASUREMENT OF RECOVERED CHARGE - $\mathbf{Q}_{\text{RA1}}$



# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Conditions		Min.	Max.	Units
V <sub>TM</sub>	Maximum on-state voltage	At 1000A peak, T <sub>case</sub> = 125°C		-	2.8	V
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At $V_{RRM}/V_{DRM}$ , $T_{case} = 125^{\circ}C$		-	80	mA
dV/dt	Maximum linear rate of rise of off-state voltage	Linear to 60% $V_{DRM}$ $T_j$ = 125°C, Gate open circuit		-	300	V/μs
dl/dt		Gate source 20V, 20Ω	Repetitive 50Hz	-	500	A/μs
di/dt	Rate of rise of on-state current	t <sub>r</sub> ≤ 0.5μs, T <sub>j</sub> = 125°C	Non-repetitive	-	800	A/μs
V <sub>T(TO)</sub>	Threshold voltage	At T <sub>vj</sub> = 125°C		-	1.8	V
r <sub>T</sub>	On-state slope resistance	At T <sub>vj</sub> = 125°C		-	1.0	mΩ
t <sub>gd</sub>	Delay time	$T_{j} = 25^{\circ}C$ , $I_{T} = 50A$ , $V_{D} = 300V$ , $I_{G} = 1A$ , $dI/dt = 50A/\mu s$ , $dI_{G}/dt = 1A/\mu s$		-	-*	μs
t <sub>(ON)TOT</sub>	Total turn-on time			-	_*	μѕ
I <sub>H</sub>	Holding current	$T_{j} = 25^{\circ}C, I_{TM} = 1A, V_{D} = 12V$		100*	-	mA
IL	Latching current	$T_{j} = 25^{\circ}\text{C}, I_{G} = 0.5\text{A}, V_{D} = 12\text{V}$		300*	-	mA
t <sub>q</sub>	Turn-off time	$ \begin{array}{l} T_{j}=125^{\circ}\text{C}, \ I_{T}=250\text{A}, \ V_{R}=50\text{V}, \\ \text{dV/dt}=20\text{V/}\mu\text{s} \ (\text{Linear to }60\% \ \text{V}_{\text{DRM}}), \\ \text{dI}_{R}/\text{dt}=50\text{A/}\mu\text{s}, \ \text{Gate open circuit} \end{array}  \   \begin{array}{l} t_{q} \ \text{code: L} \end{array} $		-	100	μѕ
Q <sub>RR</sub>	Reverse recovery charge			-	500	μС

<sup>\*</sup>Typical value.

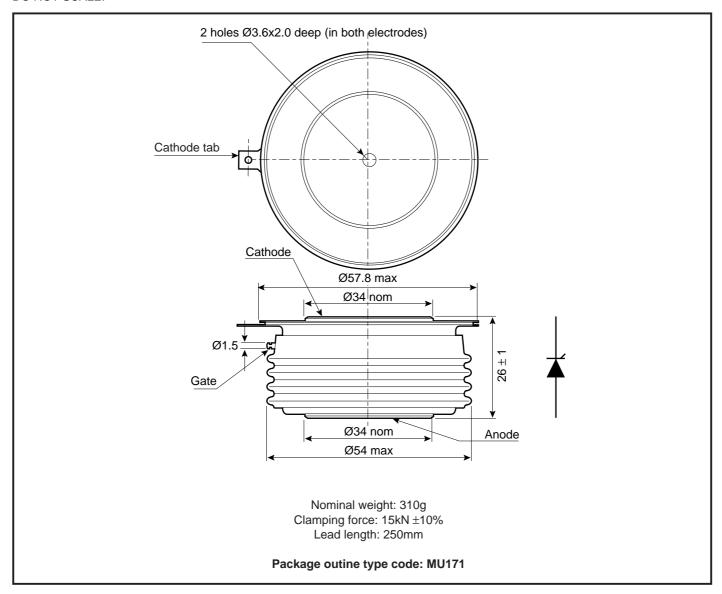
# **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Conditions	Тур.	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	$V_{DRM} = 12V, R_L = 6\Omega, T_{case} = 25^{\circ}C$	-	3.0	V
I <sub>GT</sub>	Gate trigger current	$V_{DRM} = 12V, R_{L} = 6\Omega, T_{case} = 25^{\circ}C$	-	300	mA
$V_{\sf GD}$	Gate non-trigger voltage	At $V_{DRM} T_{case} = 125^{\circ}C$ , $R_{L} = 1k\Omega$ ,	-	0.25	V
V <sub>FGM</sub>	Peak forward gate voltage	Anode positive with respect to cathode	-	30	V
$V_{FGN}$	Peak forward gate voltage	Anode negative with respect to cathode	-	0.25	V
V <sub>RGM</sub>	Peak reverse gate voltage		-	5.0	V
I <sub>FGM</sub>	Peak forward gate current	Anode positive with respect to cathode	-	10	А
P <sub>GM</sub>	Peak gate power		-	50	W
$P_{G(AV)}$	Mean gate power		-	3.0	W

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## **PACKAGE DETAILS**

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



## **ASSOCIATED PUBLICATIONS**

Title	Application Note	
	Number	
Calculating the junction temperature or power semiconductors	AN4506	
Gate triggering and the use of gate characteristics	AN4840	
Recommendations for clamping power semiconductors	AN4839	
The effect of temperature on thyristor performance	AN4870	
Thyristor and diode measurement with a multi-meter	AN4853	
Turn-on performance of thyristors in parallel	AN4999	
Use of $V_{TO}$ , $r_{T}$ on-state characteristic	AN5001	

#### POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

#### **DEVICE CLAMPS**

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of preloaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

#### **HEATSINKS**

Power Assembly has it's own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance or our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or the factory.



#### http://www.dynexsemi.com

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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

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No Annotation: The product parameters are fixed and the product is available to datasheet specification

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